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300 µA, Auto-Zeroed Op Amps

Features

- High DC Precision:
 - V_{OS} Drift: ±50 nV/°C (maximum)
 - V_{OS}: ±2 μV (maximum)
 - A_{OL}: 130 dB (minimum)
 - PSRR: 130 dB (minimum)
 - CMRR: 130 dB (minimum)
 - E_{ni} : 2.5 μV_{P-P} (typical), f = 0.1 Hz to 10 Hz
 - E_{ni}: 0.79 μVp-p (typical), f = 0.01 Hz to 1 Hz
- Low Power and Supply Voltages:
 - I_O: 300 µA/amplifier (typical)
 - Wide Supply Voltage Range: 1.8V to 5.5V
- · Easy to Use:
 - Rail-to-Rail Input/Output
 - Gain Bandwidth Product: 1.3 MHz (typical)
 - Unity Gain Stable
 - Available in Single and Dual
 - Single with Chip Select (CS): MCP6V03
- Extended Temperature Range: -40°C to +125°C

Typical Applications

- · Portable Instrumentation
- · Sensor Conditioning
- Temperature Measurement
- DC Offset Correction
- Medical Instrumentation

Design Aids

- · SPICE Macro Models
- FilterLab[®] Software
- Mindi™ Circuit Designer & Simulator
- Microchip Advanced Part Selector (MAPS)
- Analog Demonstration and Evaluation Boards
- · Application Notes

Related Parts

MCP6V06/7/8: Non-spread clock, lower noise

Description

The Microchip Technology Inc. MCP6V01/2/3 family of operational amplifiers has input offset voltage correction for very low offset and offset drift. These devices have a wide gain bandwidth product (1.3 MHz, typical) and strongly reject switching noise. They are unity gain stable, have no 1/f noise, and have good PSRR and CMRR. These products operate with a single supply voltage as low as 1.8V, while drawing 300 μ A/amplifier (typical) of quiescent current.

The Microchip Technology Inc. MCP6V01/2/3 op amps are offered in single (MCP6V01), single with Chip Select (\overline{CS}) (MCP6V03), and dual (MCP6V02). They are designed in an advanced CMOS process.

Package Types (top view)



Typical Application Circuit



1.0 ELECTRICAL CHARACTERISTICS

1.1 Absolute Maximum Ratings †

| $V_{DD} - V_{SS}$ | 6.5V |
|---|---|
| Current at Input Pins | ±2 mA |
| Analog Inputs (V _{IN} + and V _{IN} -) †† V _S | $_{SS}$ – 1.0V to V _{DD} +1.0V |
| All other Inputs and Outputs $V_{\rm S}$ | $_{SS}$ – 0.3V to V _{DD} +0.3V |
| Difference Input voltage | V _{DD} – V _{SS} |
| Output Short Circuit Current | Continuous |
| Current at Output and Supply Pins | ±30 mA |
| Storage Temperature | 65°C to +150°C |
| Max. Junction Temperature | +150°C |
| ESD protection on all pins (HBM, MM) | ≥ 4 kV, 300V |

† Notice: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

†† See Section 4.2.1 "Rail-to-Rail Inputs".

1.2 Specifications

TABLE 1-1: DC ELECTRICAL SPECIFICATIONS

| Electrical Characteristics: Unless otherwis $V_{avid} = V_{ad}/2$, $V_{ad} = V_{ad}/2$, $R_{c} = 20$ kQ to V_{c} | e indi <u>cat</u> ed, | $T_A = +25^{\circ}C$, | $V_{DD} = +1$ | 1.8V to +5.5V | , V _{SS} = G | ND, $V_{CM} = V_{DD}/3$, |
|---|-----------------------|------------------------|----------------------|------------------------|-----------------------|---|
| Parameters | Sym | Min | Тур | Max | Units | Conditions |
| Input Offset | | | | | | |
| Input Offset Voltage | V _{OS} | -2.0 | _ | +2.0 | μV | T _A = +25°C (Note 1) |
| Input Offset Voltage Drift with Temperature (linear Temp. Co.) | TC ₁ | -50 | - | +50 | nV/°C | T _A = -40 to +125°C (Note 1) |
| Input Offset Voltage Quadratic Temp. Co. | TC ₂ | _ | ±0.1 | _ | nV/°C ² | T _A = -40 to +125°C |
| Power Supply Rejection | PSRR | 130 | 143 | _ | dB | (Note 1) |
| Input Bias Current and Impedance | | | | | | |
| Input Bias Current | I _B | — | ±1 | _ | pА | |
| Input Bias Current across Temperature | I _B | _ | 60 | _ | pА | T _A = +85°C |
| | I _B | — | 600 | 5000 | pА | T _A = +125°C |
| Input Offset Current | I _{OS} | _ | -30 | _ | pА | |
| Input Offset Current across Temperature | I _{OS} | _ | -50 | _ | pА | T _A = +85°C |
| | I _{OS} | -1000 | -75 | 1000 | pА | T _A = +125°C |
| Common Mode Input Impedance | Z _{CM} | _ | 10 ¹³ 6 | _ | Ω pF | |
| Differential Input Impedance | Z _{DIFF} | _ | 10 ¹³ 6 | _ | Ω pF | |
| Common Mode | | | | | | |
| Common-Mode Input Voltage Range | V _{CMR} | $V_{SS}-0.20$ | _ | V _{DD} + 0.20 | V | (Note 2) |
| Common-Mode Rejection | CMRR | 130 | 142 | — | dB | V _{DD} = 1.8V, V _{CM} = -0.2V to 2.0V (Note 1, Note 2) |
| | CMRR | 140 | 152 | — | dB | V _{DD} = 5.5V, V _{CM} = -0.2V to 5.7V (Note 1, Note 2) |
| Open-Loop Gain | | | | | | |
| DC Open-Loop Gain (large signal) | A _{OL} | 130 | 145 | — | dB | V _{DD} = 1.8V, V _{OUT} = 0.2V to 1.6V (Note 1) |
| | A _{OL} | 140 | 156 | — | dB | V _{DD} = 5.5V, V _{OUT} = 0.2V to 5.3V (Note 1) |

Note 1: Set by design and characterization. Due to thermal junction and other effects in the production environment, these parts can only be screened in production (except TC₁; see **Appendix B: "Offset Related Test Screens"**).

2: Figure 2-18 shows how V_{CMR} changed across temperature for the first three production lots.

TABLE 1-1: DC ELECTRICAL SPECIFICATIONS (CONTINUED)

| Electrical Characteristics: Unless otherwise indicated, $T_A = +25^{\circ}C$, $V_{DD} = +1.8V$ to $+5.5V$, $V_{SS} = GND$, $V_{CM} = V_{DD}/3$, $V_{OUT} = V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 20$ k Ω to V_L , and $\overline{CS} = GND$ (refer to Figure 1-5 and Figure 1-6). | | | | | | | | | | |
|---|------------------|------|-----|------|-------|------------------------|--|--|--|--|
| Parameters | Sym | Min | Тур | Max | Units | Conditions | | | | |
| Output | | | | | | | | | | |
| Maximum Output Voltage Swing V_{OL} , V_{OH} V_{SS} + 15 - V_{DD} - 15 mV G = +2, 0.5V input overded | | | | | | | | | | |
| Output Short Circuit Current | I _{SC} | | ±7 | — | mA | V _{DD} = 1.8V | | | | |
| | I _{SC} | | ±22 | _ | mA | V _{DD} = 5.5V | | | | |
| Power Supply | | | | | | | | | | |
| Supply Voltage | V _{DD} | 1.8 | _ | 5.5 | V | | | | | |
| Quiescent Current per amplifier | Ι _Q | 200 | 300 | 400 | μA | I _O = 0 | | | | |
| POR Trip Voltage | V _{POR} | 1.15 | _ | 1.65 | V | | | | | |

Note 1: Set by design and characterization. Due to thermal junction and other effects in the production environment, these parts can only be screened in production (except TC₁; see **Appendix B: "Offset Related Test Screens"**).

2: Figure 2-18 shows how V_{CMR} changed across temperature for the first three production lots.

TABLE 1-2: AC ELECTRICAL SPECIFICATIONS

| Electrical Characteristics: Unless otherwise indicated, $T_A = +25$ °C, $V_{DD} = +1.8V$ to +5.5V, $V_{SS} = GND$, $V_{CM} = V_{DD}/3$, $V_{OUT} = V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 20$ k Ω to V_L , $C_L = 60$ pF, and $\overline{CS} = GND$ (refer to Figure 1-5 and Figure 1-6). | | | | | | | | | | |
|--|------------------|-----|------|-----|------------------|---|--|--|--|--|
| Parameters | Sym | Min | Тур | Max | Units | Conditions | | | | |
| Amplifier AC Response | | | | | | | | | | |
| Gain Bandwidth Product | GBWP | | 1.3 | | MHz | | | | | |
| Slew Rate | SR | - | 0.5 | _ | V/µs | | | | | |
| Phase Margin | PM | | 65 | | ٥ | G = +1 | | | | |
| Amplifier Noise Response | | | | | | | | | | |
| Input Noise Voltage | E _{ni} | - | 0.79 | _ | μV_{P-P} | f = 0.01 Hz to 1 Hz | | | | |
| | E _{ni} | - | 2.5 | | μV_{P-P} | f = 0.1 Hz to 10 Hz | | | | |
| Input Noise Voltage Density | e _{ni} | | 120 | | nV/√Hz | f < 2.5 kHz | | | | |
| | e _{ni} | - | 45 | | nV/√Hz | f = 100 kHz | | | | |
| Input Noise Current Density | i _{ni} | | 0.6 | | fA/√Hz | | | | | |
| Amplifier Distortion (Note 1) | | | | | | | | | | |
| Intermodulation Distortion (AC) | IMD | - | <1 | _ | μV _{PK} | V_{CM} tone = 50 m V_{PK} at 1 kHz, G_N = 1, V_{DD} = 1.8V | | | | |
| | IMD | - | <1 | _ | μV _{PK} | V_{CM} tone = 50 m V_{PK} at 1 kHz, G_N = 1, V_{DD} = 5.5V | | | | |
| Amplifier Step Response | | | | | | | | | | |
| Start Up Time | t _{STR} | - | 500 | _ | μs | V_{OS} within 50 μV of its final value | | | | |
| Offset Correction Settling Time | t _{STL} | _ | 300 | _ | μs | G = +1, V _{IN} step of 2V, V _{OS} within 50 μ V of its final value | | | | |
| Output Overdrive Recovery Time | t _{ODR} | — | 100 | _ | μs | G = -100, ± 0.5 V input overdrive to V _{DD} /2, V _{IN} 50% point to V _{OUT} 90% point (Note 2) | | | | |

Note 1: These parameters were characterized using the circuit in Figure 1-7. Figure 2-37 and Figure 2-38 show both an IMD tone at DC and a residual tone at1 kHz; all other IMD and clock tones are spread by the randomization circuitry.

2: t_{ODR} includes some uncertainty due to clock edge timing.

| TABLE 1-3: DIGITAL ELECTRICAL SPECIFICATION |
|---|
|---|

| Electrical Characteristics: Unless otherwise indicated, $T_A = \pm 25^{\circ}$ C, $V_{DD} = \pm 1.8$ V to ± 5.5 V, $V_{SS} = GND$, $V_{CM} = V_{DD}/3$, $V_{OUT} = V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 20 \text{ k}\Omega$ to V_L , $C_L = 60 \text{ pF}$, and $\overline{CS} = GND$ (refer to Figure 1-5 and Figure 1-6). | | | | | | | | | | | |
|--|---------------------|---------------------|-----------------|--------------------|-------|--|--|--|--|--|--|
| Parameters | Sym | Min | Тур | Max | Units | Conditions | | | | | |
| CS Pull-Down Resistor (MCP6V03) | | | | | | | | | | | |
| CS Pull-Down Resistor | R _{PD} | 3 | 5 | — | MΩ | | | | | | |
| CS Low Specifications (MCP6V03 |) | | | | | | | | | | |
| CS Logic Threshold, Low | VIL | V _{SS} | | $0.3V_{\text{DD}}$ | V | | | | | | |
| CS Input Current, Low | I _{CSL} | — | 5 | — | pА | $\overline{CS} = V_{SS}$ | | | | | |
| CS High Specifications (MCP6V03) | | | | | | | | | | | |
| CS Logic Threshold, High | V _{IH} | $0.7 V_{\text{DD}}$ | _ | V _{DD} | V | | | | | | |
| CS Input Current, High | I _{CSH} | — | V_{DD}/R_{PD} | _ | pА | $\overline{CS} = V_{DD}$ | | | | | |
| CS Input High, GND Current per | I _{SS} | — | -0.7 | — | μA | $\overline{\text{CS}} = \text{V}_{\text{DD}}, \text{V}_{\text{DD}} = 1.8\text{V}$ | | | | | |
| amplifier | I _{SS} | — | -2.3 | — | μA | $\overline{\text{CS}}$ = V _{DD} , V _{DD} = 5.5V | | | | | |
| Amplifier Output Leakage, CS High | I _{O_LEAK} | — | 20 | — | pА | $\overline{CS} = V_{DD}$ | | | | | |
| CS Dynamic Specifications (MCP6V03) | | | | | | | | | | | |
| CS Low to Amplifier Output On Turn-on Time | t _{ON} | — | 11 | 100 | μs | $\overline{\text{CS}} \text{ Low} = \text{V}_{\text{SS}} + 0.3 \text{ V}, \text{ G} = +1 \text{ V/V},$ $\text{V}_{\text{OUT}} = 0.9 \text{ V}_{\text{DD}}/2$ | | | | | |
| CS High to Amplifier Output High-Z | t _{OFF} | — | 10 | — | μs | $\overline{CS} High = V_{DD} - 0.3 V, G = +1 V/V,$ $V_{OUT} = 0.1 V_{DD}/2$ | | | | | |
| Internal Hysteresis | V _{HYST} | _ | 0.25 | _ | V | | | | | | |

| TABLE 1-4: TEMPERATURE SPECIFICATIONS | | | | | | | | | |
|---|----------------|-----|-----|------|-------|------------|--|--|--|
| Electrical Characteristics: Unless otherwise indicated, all limits are specified for: V_{DD} = +1.8V to +5.5V, V_{SS} = GND. | | | | | | | | | |
| Parameters | Sym | Min | Тур | Max | Units | Conditions | | | |
| Temperature Ranges | | | | | | | | | |
| Specified Temperature Range | T _A | -40 | — | +125 | °C | | | | |
| Operating Temperature Range | T _A | -40 | — | +125 | °C | (Note 1) | | | |
| Storage Temperature Range | T _A | -65 | — | +150 | °C | | | | |
| Thermal Package Resistances | | | | | | | | | |
| Thermal Resistance, 8L-2x3 TDFN | θ_{JA} | _ | 41 | — | °C/W | | | | |
| Thermal Resistance, 8L-4x4 DFN | θ_{JA} | _ | 44 | _ | °C/W | (Note 2) | | | |

150

°C/W

Note 1: Operation must not cause $T_{\rm J}$ to exceed Maximum Junction Temperature specification (150 $^{\circ}\text{C}).$

 θ_{JA}

2: Measured on a standard JC51-7, four layer printed circuit board with ground plane and vias.

Thermal Resistance, 8L-SOIC

1.3 Timing Diagrams



FIGURE 1-1: Amplifier Start Up.



FIGURE 1-2: Time.



FIGURE 1-3:

Output Overdrive Recovery.

Offset Correction Settling



1.4 Test Circuits

The circuits used for the DC and AC tests are shown in Figure 1-5 and Figure 1-6. Lay the bypass capacitors out as discussed in **Section 4.3.8** "Supply Bypassing and Filtering". R_N is equal to the parallel combination of R_F and R_G to minimize bias current effects.



FIGURE 1-5: AC and DC Test Circuit for Most Non-Inverting Gain Conditions.



FIGURE 1-6: AC and DC Test Circuit for Most Inverting Gain Conditions.

The circuit in Figure 1-7 tests the op amp input's dynamic behavior (i.e., IMD, t_{STR} , t_{STL} and t_{ODR}). The potentiometer balances the resistor network (V_{OUT} should equal V_{REF} at DC). The op amp's common mode input voltage is V_{CM} = V_{IN}/2. The error at the input (V_{ERR}) appears at V_{OUT} with a noise gain of 10 V/V.



FIGURE 1-7: Test Circuit for Dynamic Input Behavior.

2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$, $V_{DD} = +1.8V$ to 5.5V, $V_{SS} = GND$, $V_{CM} = V_{DD}/3$, $V_{OUT} = V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 20 \text{ k}\Omega$ to V_L , $C_L = 60 \text{ pF}$, and $\overline{CS} = GND$.

2.1 DC Input Precision



FIGURE 2-1:

Input Offset Voltage.



FIGURE 2-2:









FIGURE 2-4: Input Offset Voltage vs. Power Supply Voltage with $V_{CM} = V_{CMR \ L}$.



FIGURE 2-5: Input Offset Voltage vs. Power Supply Voltage with $V_{CM} = V_{CMR}$ H·



FIGURE 2-6: Output Voltage.

Input Offset Voltage vs.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$, $V_{DD} = +1.8V$ to 5.5V, $V_{SS} = GND$, $V_{CM} = V_{DD}/3$, $V_{OUT} = V_{DD}/2$, V_L = $V_{DD}/2,\,R_L$ = 20 k Ω to $V_L,\,C_L$ = 60 pF, and \overline{CS} = GND.



FIGURE 2-7: Input Offset Voltage vs. Common Mode Voltage with $V_{DD} = 1.8V$.



FIGURE 2-8: Input Offset Voltage vs. Common Mode Voltage with $V_{DD} = 5.5V$.



FIGURE 2-9:







FIGURE 2-11: DC Open-Loop Gain.



FIGURE 2-12: CMRR and PSRR vs. Ambient Temperature.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$, $V_{DD} = +1.8V$ to 5.5V, $V_{SS} = GND$, $V_{CM} = V_{DD}/3$, $V_{OUT} = V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 20 \text{ k}\Omega$ to V_L , $C_L = 60 \text{ pF}$, and $\overline{CS} = GND$.



FIGURE 2-13: DC Open-Loop Gain vs. Ambient Temperature.



FIGURE 2-14: Input Bias and Offset Currents vs. Common Mode Input Voltage with $T_A = +85$ °C.



FIGURE 2-15: Input Bias and Offset Currents vs. Common Mode Input Voltage with $T_A = +125$ °C.



FIGURE 2-16: Input Bias and Offset Currents vs. Ambient Temperature with $V_{DD} = +5.5V.$



FIGURE 2-17: Input Bias Current vs. Input Voltage (below V_{SS}).

Note: Unless otherwise indicated, T_A = +25°C, V_{DD} = +1.8V to 5.5V, V_{SS} = GND, V_{CM} = $V_{DD}/3$, V_{OUT} = $V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 20 \text{ k}\Omega$ to V_L , $C_L = 60 \text{ pF}$, and $\overline{CS} = \text{GND}$.

2.2 **Other DC Voltages and Currents**



FIGURE 2-18: Input Common Mode Voltage Headroom (Range) vs. Ambient Temperature.



FIGURE 2-19: Output Voltage Headroom vs. Output Current.



FIGURE 2-20: Output Voltage Headroom vs. Ambient Temperature.



FIGURE 2-21: Output Short Circuit Current vs. Power Supply Voltage.



FIGURE 2-22: Supply Current vs. Power Supply Voltage.



Voltage.

Power On Reset Trip

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$, $V_{DD} = +1.8V$ to 5.5V, $V_{SS} = GND$, $V_{CM} = V_{DD}/3$, $V_{OUT} = V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 20 \text{ k}\Omega$ to V_L , $C_L = 60 \text{ pF}$, and $\overline{CS} = GND$.



FIGURE 2-24: Power On Reset Voltage vs. Ambient Temperature.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$, $V_{DD} = +1.8V$ to 5.5V, $V_{SS} = GND$, $V_{CM} = V_{DD}/3$, $V_{OUT} = V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 20 \text{ k}\Omega$ to V_L , $C_L = 60 \text{ pF}$, and $\overline{CS} = GND$.

2.3 Frequency Response



FIGURE 2-25: CMRR and PSRR vs. Frequency.



FIGURE 2-26: Open-Loop Gain vs. Frequency with $V_{DD} = 1.8V$.



FIGURE 2-27: Open-Loop Gain vs. Frequency with $V_{DD} = 5.5V$.



FIGURE 2-28: Gain Bandwidth Product and Phase Margin vs. Ambient Temperature.



FIGURE 2-29: Gain Bandwidth Product and Phase Margin vs. Common Mode Input Voltage.



FIGURE 2-30: Gain Bandwidth Product and Phase Margin vs. Output Voltage.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$, $V_{DD} = +1.8V$ to 5.5V, $V_{SS} = GND$, $V_{CM} = V_{DD}/3$, $V_{OUT} = V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 20 \text{ k}\Omega$ to V_L , $C_L = 60 \text{ pF}$, and $\overline{CS} = GND$.



FIGURE 2-31:Closed-Loop OutputImpedance vs. Frequency with $V_{DD} = 1.8V.$



FIGURE 2-32: Closed-Loop Output Impedance vs. Frequency with $V_{DD} = 5.5V$.



FIGURE 2-33: Channel-to-Channel Separation vs. Frequency.



FIGURE 2-34: Maximum Output Voltage Swing vs. Frequency.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$, $V_{DD} = +1.8V$ to 5.5V, $V_{SS} = GND$, $V_{CM} = V_{DD}/3$, $V_{OUT} = V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 20 \text{ k}\Omega$ to V_L , $C_L = 60 \text{ pF}$, and $\overline{CS} = GND$.

2.4 Input Noise and Distortion



FIGURE 2-35: vs. Frequency.

Input Noise Voltage Density



FIGURE 2-36: Input Noise Voltage Density vs. Input Common Mode Voltage.



FIGURE 2-37: Inter-Modulation Distortion vs. Frequency with V_{CM} Disturbance (see Figure 1-7).



FIGURE 2-38: Inter-Modulation Distortion vs. Frequency with V_{DD} Disturbance (see Figure 1-7).



FIGURE 2-39: Input Noise vs. Time with 1 Hz and 10 Hz Filters and $V_{DD} = 1.8V$.



FIGURE 2-40: Input Noise vs. Time with 1 Hz and 10 Hz Filters and $V_{DD} = 5.5V$.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$, $V_{DD} = +1.8V$ to 5.5V, $V_{SS} = GND$, $V_{CM} = V_{DD}/3$, $V_{OUT} = V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 20 \text{ k}\Omega$ to V_L , $C_L = 60 \text{ pF}$, and $\overline{CS} = GND$.

2.5 Time Response



FIGURE 2-41: Input Offset Voltage vs. Time with Temperature Change.



FIGURE 2-42: Input Offset Voltage vs. Time at Power Up.



FIGURE 2-43: The MCP6V01/2/3 family shows no input phase reversal with overdrive.



FIGURE 2-44: Non-inverting Small Signal Step Response.



FIGURE 2-45: Non-inverting Large Signal Step Response.



FIGURE 2-46: Inv Response.

Inverting Small Signal Step

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$, $V_{DD} = +1.8V$ to 5.5V, $V_{SS} = GND$, $V_{CM} = V_{DD}/3$, $V_{OUT} = V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 20 \text{ k}\Omega$ to V_L , $C_L = 60 \text{ pF}$, and $\overline{CS} = GND$.



FIGURE 2-47: Inverting Large Signal Step Response.



FIGURE 2-48: Slew Rate vs. Ambient Temperature.



FIGURE 2-49: Output Overdrive Recovery vs. Time with G = -100 V/V.



FIGURE 2-50: Output Overdrive Recovery Time vs. Inverting Gain.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$, $V_{DD} = +1.8V$ to 5.5V, $V_{SS} = GND$, $V_{CM} = V_{DD}/3$, $V_{OUT} = V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 20 \text{ k}\Omega$ to V_L , $C_L = 60 \text{ pF}$, and $\overline{CS} = GND$.

2.6 Chip Select Response (MCP6V03 only)



FIGURE 2-51: Chip Select Current vs. Power Supply Voltage.



FIGURE 2-52: Power Supply Current vs. Chip Select Voltage with $V_{DD} = 1.8V$.



FIGURE 2-53: Power Supply Current vs. Chip Select Voltage with $V_{DD} = 5.5V$.



FIGURE 2-54: Chip Select Current vs. Chip Select Voltage.



FIGURE 2-55: Chip Select Voltage, Output Voltage vs. Time with $V_{DD} = 1.8V$.



FIGURE 2-56: Chip Select Voltage, Output Voltage vs. Time with $V_{DD} = 5.5V$.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$, $V_{DD} = +1.8V$ to 5.5V, $V_{SS} = GND$, $V_{CM} = V_{DD}/3$, $V_{OUT} = V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 20 \text{ k}\Omega$ to V_L , $C_L = 60 \text{ pF}$, and $\overline{CS} = GND$.



FIGURE 2-57: Chip Select Relative Logic Thresholds vs. Ambient Temperature.



FIGURE 2-58: Chip Select Hysteresis.



FIGURE 2-59: Chip Select Turn On Time vs. Ambient Temperature.



FIGURE 2-60: Chip Select's Pull-down Resistor (R_{PD}) vs. Ambient Temperature.



FIGURE 2-61: Quiescent Current in Shutdown vs. Power Supply Voltage.

3.0 PIN DESCRIPTIONS

Descriptions of the pins are listed in Table 3-1.

| MCP | 6V01 | МСР | MCP6V02 | | 6V03 | Cumhal | Description | |
|---------|---------|-----|---------|---------|------|---------------------------------------|---|--|
| TDFN | SOIC | DFN | SOIC | TDFN | SOIC | Symbol | Description | |
| 6 | 6 | 1 | 1 | 6 | 6 | V _{OUT} , V _{OUTA} | Output (op amp A) | |
| 2 | 2 | 2 | 2 | 2 | 2 | V _{IN} -, V _{INA} - | Inverting Input (op amp A) | |
| 3 | 3 | 3 | 3 | 3 | 3 | V _{IN} +, V _{INA} + | Non-inverting Input (op amp A) | |
| 4 | 4 | 4 | 4 | 4 | 4 | V _{SS} | Negative Power Supply | |
| — | — | 5 | 5 | — | | V _{INB} + | Non-inverting Input (op amp B) | |
| _ | _ | 6 | 6 | — | _ | V _{INB} – | Inverting Input (op amp B) | |
| — | — | 7 | 7 | — | _ | V _{OUTB} | Output (op amp B) | |
| 7 | 7 | 8 | 8 | 7 | 7 | V _{DD} | Positive Power Supply | |
| — | — | _ | | — | 8 | CS | Chip Select (op amp A) | |
| 1, 5, 8 | 1, 5, 8 | | | 1, 5, 8 | 1, 5 | NC | No Internal Connection | |
| 9 | _ | 9 | — | 9 | _ | EP | Exposed Thermal Pad (EP); must be connected to V _{SS} | |

TABLE 3-1: PIN FUNCTION TABLE

3.1 Analog Outputs

The analog output pins (V_{OUT}) are low-impedance voltage sources.

3.2 Analog Inputs

The non-inverting and inverting inputs (V_{IN}+, V_{IN}-, ...) are high-impedance CMOS inputs with low bias currents.

3.3 Power Supply Pins

The positive power supply (V_{DD}) is 1.8V to 5.5V higher than the negative power supply (V_{SS}). For normal operation, the other pins are between V_{SS} and V_{DD}.

Typically, these parts are used in a single (positive) supply configuration. In this case, V_{SS} is connected to ground and V_{DD} is connected to the supply. V_{DD} will need bypass capacitors.

3.4 Chip Select (CS) Digital Input

This pin (\overline{CS}) is a CMOS, Schmitt-triggered input that places the MCP6V03 op amps into a low power mode of operation.

3.5 Exposed Thermal Pad (EP)

There is an internal connection between the Exposed Thermal Pad (EP) and the V_{SS} pin; they must be connected to the same potential on the Printed Circuit Board (PCB).

This pad can be connected to a PCB ground plane to provide a larger heat sink. This improves the package thermal resistance (θ_{JA}).

NOTES:

4.0 APPLICATIONS

The MCP6V01/2/3 family of auto-zeroed op amps is manufactured using Microchip's state of the art CMOS process. It is designed for low cost, low power and high precision applications. Its low supply voltage, low quiescent current and wide bandwidth makes the MCP6V01/2/3 ideal for battery-powered applications.

4.1 Overview of Auto-zeroing Operation

Figure 4-1 shows a simplified diagram of the MCP6V01/2/3 auto-zeroed op amps. This will be used to explain how the DC voltage errors are reduced in this architecture.



FIGURE 4-1: Simplified Auto-zeroed Op Amp Functional Diagram.

4.1.1 BUILDING BLOCKS

The Null Amp. and Main Amp. are designed for high gain and accuracy using a differential topology. They have an auxiliary input (bottom left) used for correcting the offset voltages. Both inputs are added together internally. The capacitors at the auxiliary inputs (C_{FW} and C_{H}) hold the corrected values during normal operation.

The Output Buffer is designed to drive external loads at the V_{OUT} pin. It also produces a single ended output voltage (V_{REF} is an internal reference voltage).

All of these switches are make-before-break in order to minimize glitch-induced errors. They are driven by two clock phases (ϕ_1 and ϕ_2) that select between normal mode and auto-zeroing mode.

The clock is derived from an internal R-C oscillator running at a rate of f_{OSC1} = 300 kHz. The oscillator's output is divided down to the desired rate. It is also randomized to minimize (spread) undesired clock tones in the output.

The internal POR ensures the part starts up in a known good state. It also provides protection against power supply brown out events.

The Chip Select input places the op amp in a low power state when it is high. When it goes low, it powers the op amp at its normal level and starts operation properly.

The Digital Control circuitry takes care of all of the housekeeping details of the switching operation. It also takes care of Chip Select and POR events.

4.1.2 AUTO-ZEROING ACTION

Figure 4-2 shows the connections between amplifiers during the Normal Mode of operation (ϕ_1). The hold capacitor (C_H) corrects the Null Amplifier's input offset. Since the Null Amplifier has very high gain, it dominates the signal seen by the Main Amplifier. This greatly reduces the impact of the Main Amplifier's input

offset voltage on overall performance. Essentially, the Null Amplifier and Main Amplifier behave as a regular op amp with very high gain (A_{OL}) and very low offset voltage (V_{OS}).





Figure 4-3 shows the connections between amplifiers during the Auto-zeroing Mode of operation (ϕ_2). The signal goes directly through the Main Amplifier, and the flywheel capacitor (C_{FW}) maintains a constant correction on the Main Amplifier's offset.

The Null Amplifier uses its own high open loop gain to drive the voltage across $C_{\rm H}$ to the point where its input offset voltage is almost zero. Because the principal input is connected to $V_{\rm IN}$ +, the auto-zeroing action corrects the offset at the current common mode input voltage ($V_{\rm CM}$) and supply voltage ($V_{\rm DD}$). This makes the DC CMRR and PSRR very high also.

Since these corrections happen every 100 $\mu s,$ or so, we also minimize slow errors, including offset drift with temperature ($\Delta V_{OS}/\Delta T_A),~1/f$ noise, and input offset aging.



FIGURE 4-3: Auto-zeroing Mode of Operation (ϕ_2) ; Equivalent Diagram.

4.1.3 INTERMODULATION DISTORTION (IMD)

The MCP6V01/2/3 op amps will show intermodulation distortion (IMD), products when an AC signal is present.

The signal and clock can be decomposed into sine wave tones (Fourier series components). These tones interact with the auto-zeroing circuitry's non-linear

response to produce IMD tones at sum and difference frequencies. IMD distortion tones are generated about all of the square wave clock's harmonics.

Clock randomization spreads the IMD tones across the frequency spectrum, but cannot eliminate them. The spread energy is low and is not correlated with the signal of interest, so it is not of concern for most precision applications. See Figure 2-37 and Figure 2-38.

4.2 Other Functional Blocks

4.2.1 RAIL-TO-RAIL INPUTS

The input stage of the MCP6V01/2/3 op amps uses two differential CMOS input stages in parallel. One operates at low common mode input voltage (V_{CM}, which is approximately equal to V_{IN}+ and V_{IN}- in normal operation) and the other at high V_{CM}. With this topology, the input operates with V_{CM} up to 0.2V past either supply rail at +25°C (see Figure 2-18). The input offset voltage (V_{OS}) is measured at V_{CM} = V_{SS} - 0.2V and V_{DD} + 0.2V to ensure proper operation.

The transition between the input stages occurs when $V_{CM} \approx V_{DD} - 0.9V$ (see Figure 2-7 and Figure 2-8). For the best distortion and gain linearity, with non-inverting gains, avoid this region of operation.

4.2.1.1 Phase Reversal

The input devices are designed to not exhibit phase inversion when the input pins exceed the supply voltages. Figure 2-43 shows an input voltage exceeding both supplies with no phase inversion.

4.2.1.2 Input Voltage and Current Limits

The ESD protection on the inputs can be depicted as shown in Figure 4-4. This structure was chosen to protect the input transistors, and to minimize input bias current (I_B). The input ESD diodes clamp the inputs when they try to go more than one diode drop below V_{SS} . They also clamp any voltages that go too far above V_{DD} ; their breakdown voltage is high enough to allow normal operation, and low enough to bypass quick ESD events within the specified limits.



FIGURE 4-4: Simplified Analog Input ESD Structures.

In order to prevent damage and/or improper operation of these amplifiers, the circuit must limit the currents (and voltages) at the input pins (see **Section 1.1** "**Absolute Maximum Ratings †**"). Figure 4-5 shows the recommended approach to protecting these inputs. The internal ESD diodes prevent the input pins (V_{IN}+ and V_{IN}-) from going too far below ground, and the resistors R₁ and R₂ limit the possible current drawn out of the input pins. Diodes D₁ and D₂ prevent the input

pins (V_{IN}+ and V_{IN}-) from going too far above V_{DD}, and dump any currents onto V_{DD}. When implemented as shown, resistors R_1 and R_2 also limit the current through D_1 and D_2 .



FIGURE 4-5: Protecting the Analog Inputs.

It is also possible to connect the diodes to the left of the resistor R₁ and R₂. In this case, the currents through the diodes D₁ and D₂ need to be limited by some other mechanism. The resistors then serve as in-rush current limiters; the DC current into the input pins (V_{IN}+ and V_{IN}-) should be very small.

A significant amount of current can flow out of the inputs (through the ESD diodes) when the common mode voltage (V_{CM}) is below ground (V_{SS}); see Figure 2-17. Applications that are high impedance may need to limit the usable voltage range.

4.2.2 RAIL-TO-RAIL OUTPUT

The output voltage range of the MCP6V01/2/3 auto-zeroed op amps is $V_{DD} - 15 \text{ mV}$ (minimum) and $V_{SS} + 15 \text{ mV}$ (maximum) when $R_L = 20 \text{ k}\Omega$ is connected to $V_{DD}/2$ and $V_{DD} = 5.5\text{V}$. Refer to Figure 2-19 and Figure 2-20 for more information.

These op amps are designed to drive light loads; use another amplifier to buffer the output from heavy loads.

4.2.3 CHIP SELECT (CS)

The single MCP6V03 has a Chip Select (\overline{CS}) pin. When \overline{CS} is pulled high, the supply current for the corresponding op amp drops to about 1 µA (typical), and is pulled through the CS pin to V_{SS}. When this happens, the amplifier is put into a high impedance state. By pulling \overline{CS} low, the amplifier is enabled. If the \overline{CS} pin is left floating, the internal pull-down resistor (about 5 MΩ) will keep the part on. Figure 1-4 shows the output voltage and supply current response to a \overline{CS} pulse.

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4.3 Application Tips

4.3.1 INPUT OFFSET VOLTAGE OVER TEMPERATURE

Table 1-1 gives both the linear and quadratic temperature coefficients (TC₁ and TC₂) of input offset voltage. The input offset voltage, at any temperature in the specified range, can be calculated as follows:

 $V_{OS}(T_A) = V_{OS} + TC_1 \Delta T + TC_2 \Delta T^2$

EQUATION 4-1:

Where:

 $\begin{array}{rcl} & & & & & \\ & & & & & \\ & & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\$

4.3.2 DC GAIN PLOTS

Figure 2-9, Figure 2-10 and Figure 2-11 are histograms of the reciprocals (in units of μ V/V) of CMRR, PSRR and A_{OL}, respectively. They represent the change in input offset voltage (V_{OS}) with a change in common mode input voltage (V_{CM}), power supply voltage (V_{DD}) and output voltage (V_{OUT}).

The $1/A_{OL}$ histogram is centered near 0 μ V/V because the measurements are dominated by the op amp's input noise. The negative values shown represent noise, *not* unstable behavior. We validate the op amps' stability by making multiple measurements of V_{OS}; instability would manifest itself as a greater unexplained variability in V_{OS} or as the railing of the output.

4.3.3 SOURCE RESISTANCES

The input bias currents have two significant components; switching glitches that dominate at room temperature and below, and input ESD diode leakage currents that dominate at +85°C and above.

Make the resistances seen by the inputs small and equal. This minimizes the output offset caused by the input bias currents.

The inputs should see a resistance on the order of 10Ω to 1 k Ω at high frequencies (i.e., above 1 MHz). This helps minimize the impact of switching glitches, which are very fast, on overall performance. In some cases, it may be necessary to add resistors in series with the inputs to achieve this improvement in performance.

4.3.4 SOURCE CAPACITANCE

The capacitances seen by the two inputs should be small and matched. The internal switches connected to the inputs dump charges on these capacitors; an offset can be created if the capacitances do not match.

4.3.5 CAPACITIVE LOADS

Driving large capacitive loads can cause stability problems for voltage feedback op amps. As the load capacitance increases, the feedback loop's phase margin decreases and the closed-loop bandwidth is reduced. This produces gain peaking in the frequency response, with overshoot and ringing in the step response. These auto-zeroed op amps have a different output impedance than most op amps, due to their unique topology.

When driving a capacitive load with these op amps, a series resistor at the output (R_{ISO} in Figure 4-6) improves the feedback loop's phase margin (stability) by making the output load resistive at higher frequencies. The bandwidth will be generally lower than the bandwidth with no capacitive load.



FIGURE 4-6: Output Resistor, R_{ISO}, Stabilizes Capacitive Loads.

Figure 4-7 gives recommended $\mathsf{R}_{\mathsf{ISO}}$ values for different capacitive loads and is independent of the gain.



FIGURE 4-7: Recommended R_{ISO} values for Capacitive Loads.

After selecting R_{ISO} for your circuit, double check the resulting frequency response peaking and step response overshoot. Modify R_{ISO} 's value until the response is reasonable. Bench evaluation and simulations with the MCP6V01 SPICE macro model (good for all of the MCP6V01/2/3 op amps) are helpful.

4.3.6 STABILIZING OUTPUT LOADS

This family of auto-zeroed op amps has an output impedance (Figure 2-31 and Figure 2-32) that has a double zero when the gain is low. This can cause a large phase shift in feedback networks that have low resistance near the part's bandwidth. This large phase shift can cause stability problems.

Figure 4-8 shows one circuit example that has low resistance near the part's bandwidth. R_F and C_F set a pole at 0.16 kHz, so the noise gain (G_N) is 1 V/V at the circuit's bandwidth (roughly 1.3 MHz). The load seen by the op amp's output at 1.3 MHz is $R_G||R_L$ (99 Ω). This is low enough to be a real concern.





Output Load Issue.

To solve this problem, increase the resistive load to at least 3 k Ω . Methods to accomplish this task include:

- Increase R_G
- Remove C_F (relocate the filter)
- Add a 3 kΩ resistor at the op amp's output that is not in the signal path; see Figure 4-9



One Solution To Output

FIGURE 4-9: Load Issue.

4.3.7 REDUCING UNDESIRED NOISE AND SIGNALS

Reduce undesired noise and signals with:

- · Low bandwidth signal filters:
 - Minimizes random analog noise
 - Reduces interfering signals
- · Good PCB layout techniques:
 - Minimizes crosstalk
 - Minimizes parasitic capacitances and inductances that interact with fast switching edges
- · Good power supply design:
 - Isolation from other parts
 - Filtering of interference on supply line(s)

4.3.8 SUPPLY BYPASSING AND FILTERING

With this family of operational amplifiers, the power supply pin (V_{DD} for single supply) should have a local bypass capacitor (i.e., 0.01 μ F to 0.1 μ F) within 2 mm of the pin for good high-frequency performance.

These parts also need a bulk capacitor (i.e., $1 \mu F$ or larger) within 100 mm to provide large, slow currents. This bulk capacitor can be shared with other low noise, analog parts.

Additional filtering of high frequency power supply noise (e.g., switched mode power supplies) can be achieved using resistors. The resistors need to be small enough to prevent a large drop in V_{DD} for the op amp, which would cause a reduced output range and possible load-induced power supply noise. The resistors also need to be large enough to dissipate little power when V_{DD} is turned on and off quickly. The circuit in Figure 4-10 gives good rejection out to 1 MHz for switched mode power supplies. Smaller resistors and capacitors are a better choice for designs where the power supply is reasonably quiet.



FIGURE 4-10: Additional Supply Filtering.